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(54) **Title:** MEMORY ARRAYS AND METHODS USED IN FORMING A MEMORY ARRAY COMPRISING STRINGS OF MEM-
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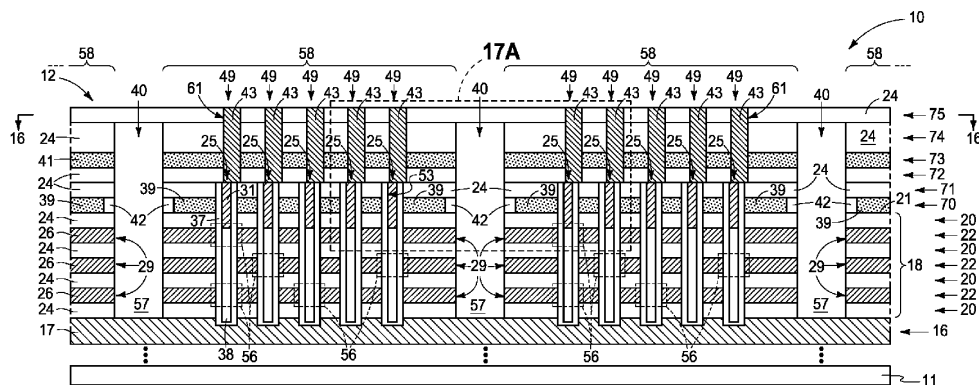


FIG. 17

(57) **Abstract:** A method used in forming a memory array comprises forming a stack comprising vertically- alternating first tiers and second tiers. A first insulator tier is above the stack. First insulator material of the first insulator tier comprises at least one of (a) and (b), where (a): silicon, nitrogen, and one or more of carbon, oxygen, boron, and phosphorus, and (b): silicon carbide. Channel-material strings are in the stack and in the first insulator tier. Conducting material is in the first insulator tier directly against sides of individual of the channel-material strings. A second insulator tier is formed above the first insulator tier and the conducting material. Second insulator material of the second insulator tier comprises at least one of the (a) and the (b). Conductive vias are formed and extend through the second insulator tier and that are individually directly electrically coupled to the individual channel-material strings through the conducting material. Other aspects, including structure independent of method, are disclosed.

[Continued on next page]

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